Description

JMT P-channel Enhancement Mode Power MOSFET

Features

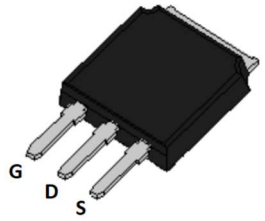
- V_{DS}= -30V, I_D= -60A
  $R_{DS(ON)}$ <7.5mΩ @ V_{GS} = -10V
  $R_{DS(ON)}$ <12.6mΩ @ V_{GS} = -4.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

Application

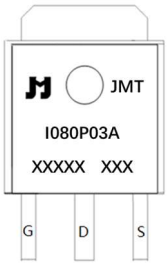
- PWM Applications
- Load Switch
- Power Management

RoHS

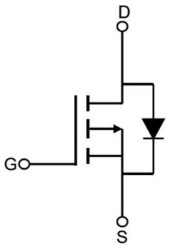
100% UIS TESTED!
100% ΔVds TESTED!



TO-251-4R top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	TUBE (PCS)	Inner Box (PCS)	Per Carton (PCS)
JMTI080P03A	JMTI080P03A	TUBE	TO-251-4R	75	4,950	29,700

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25℃	-60	A
		T_C = 100℃	-39	A
I_{DM}	Pulsed Drain Current note1		-240	A
E_{AS}	Single Pulsed Avalanche Energy note2		144	mJ
P_D	Power Dissipation	T_C = 25℃	54	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.8	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	℃

Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -30V, V_{GS}=0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}= ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}= -10V, I_D= -30A	-	5.8	7.5	mΩ
		V_{GS}= -4.5V, I_D= -20A	-	9	12.6	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= -15V, V_{GS}=0V, f=1.0MHz	-	4650	-	pF
C_{oss}	Output Capacitance		-	550	-	pF
C_{rss}	Reverse Transfer Capacitance		-	486	-	pF
Q_g	Total Gate Charge	V_{DS}= -15V, I_D= -20A, V_{GS}= -10V	-	45	-	nC
Q_{gs}	Gate-Source Charge		-	8	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	12	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}= -15V, I_D= -30A, V_{GS}= -10V, R_{GEN}=2.5Ω	-	19	-	ns
t_r	Turn-on Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	65	-	ns
t_f	Turn-off Fall Time		-	36	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-60	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-240	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -30A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. E_{AS} condition: T_J=25℃, V_{DD}= -15V, V_G= -10V, R_G=25Ω, L=0.5mH, I_{AS}= -24A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure1: Output Characteristics

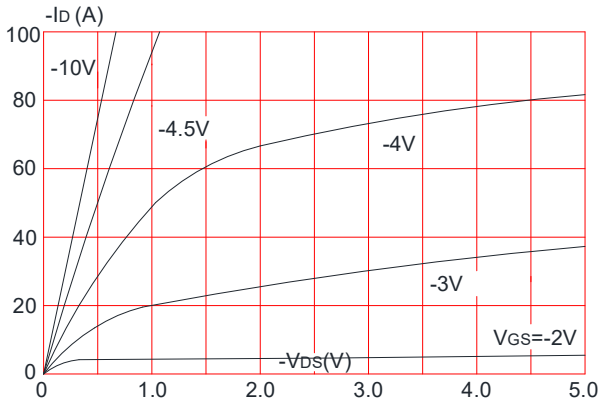


Figure 2: Typical Transfer Characteristics

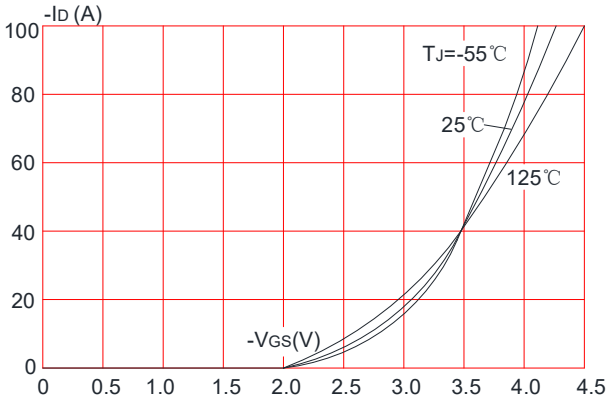


Figure 3: On-resistance vs. Drain Current

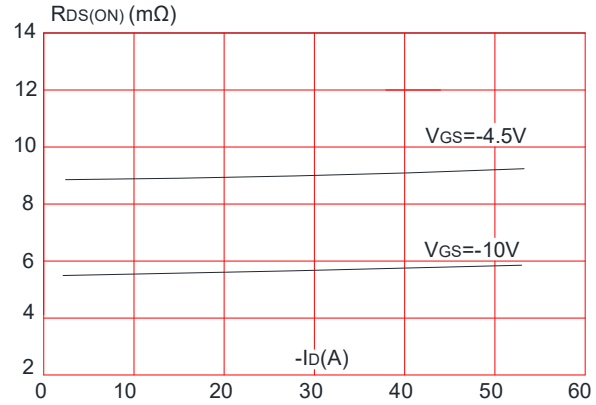


Figure 4: Body Diode Characteristics

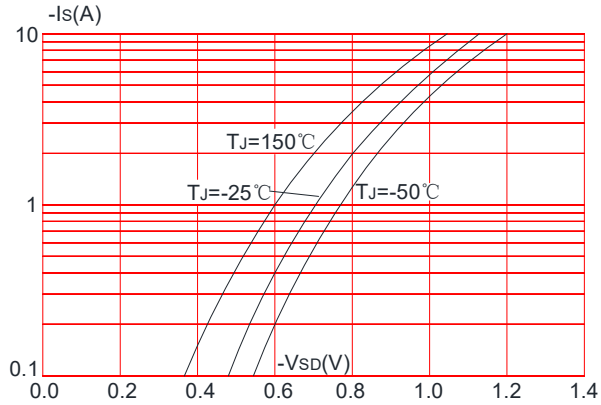


Figure 5: Gate Charge Characteristics

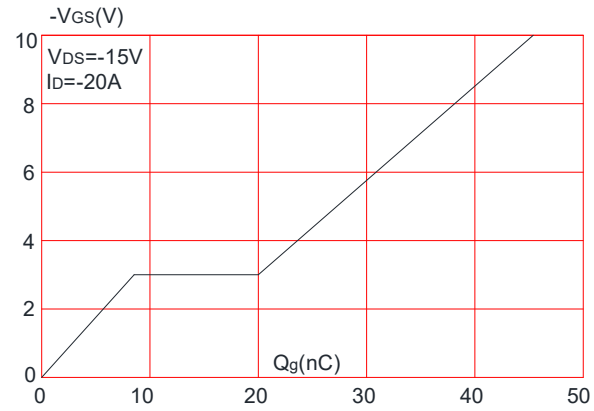


Figure 6: Capacitance Characteristics

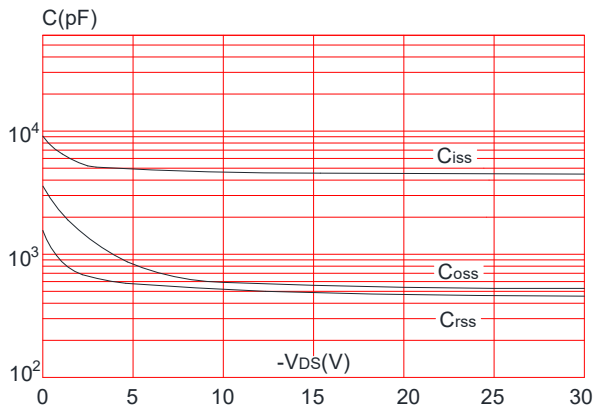


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

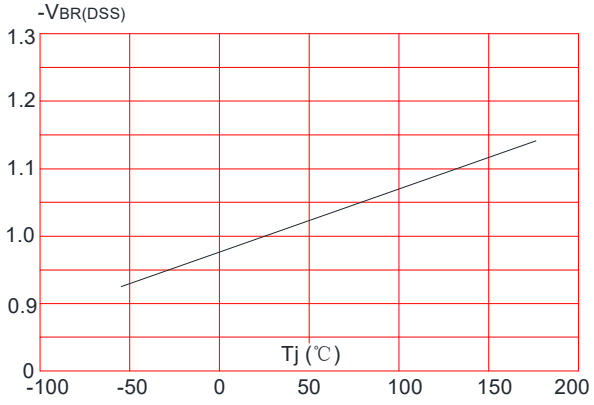


Figure 8: Normalized on Resistance vs. Junction Temperature

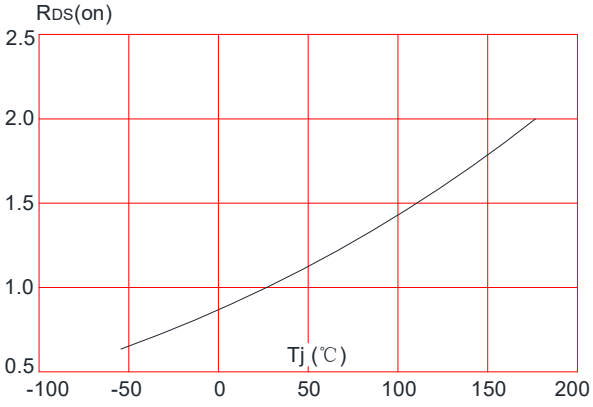


Figure 9: Maximum Safe Operating Area

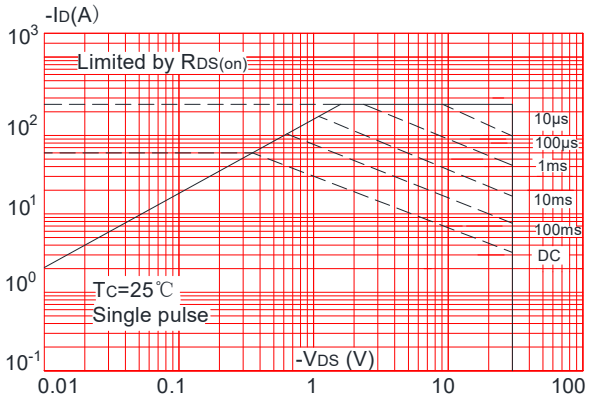


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

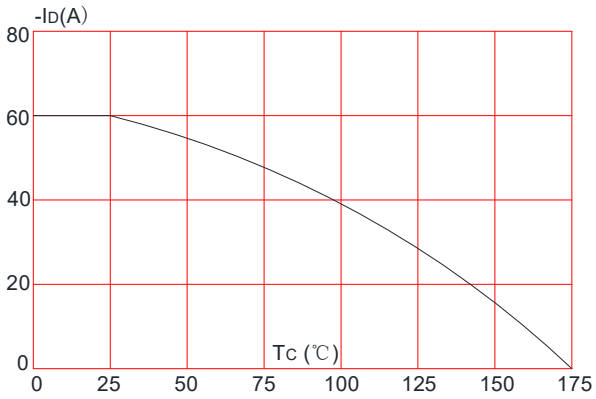
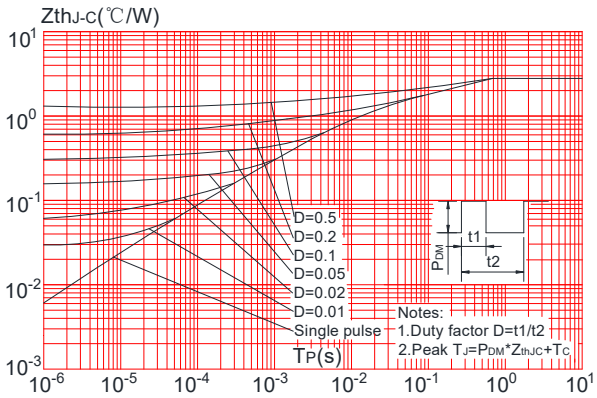
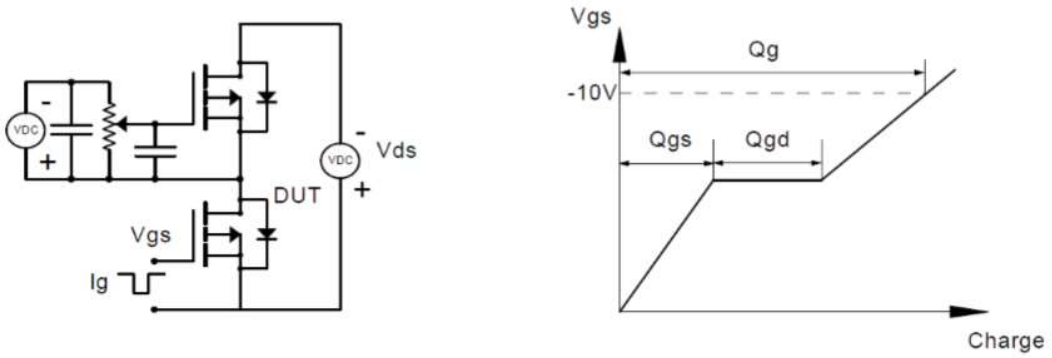


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

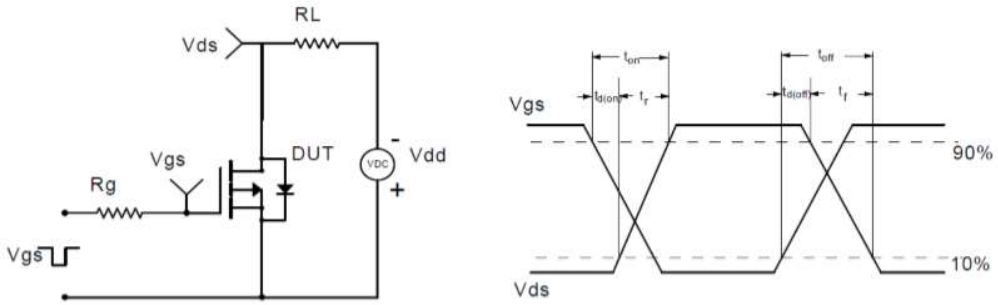


Test Circuit

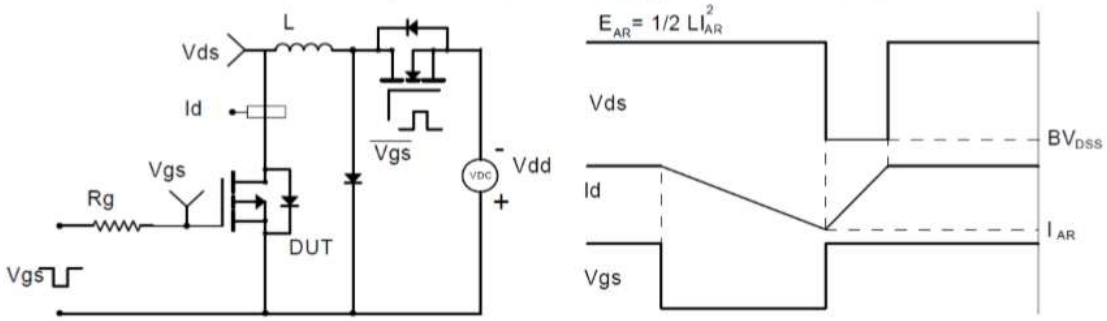
Gate Charge Test Circuit & Waveform



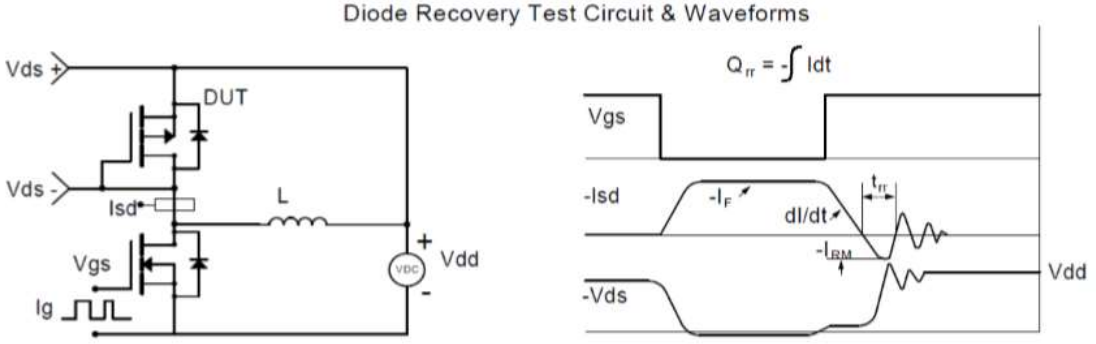
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Mechanical Data- TO-251-4R